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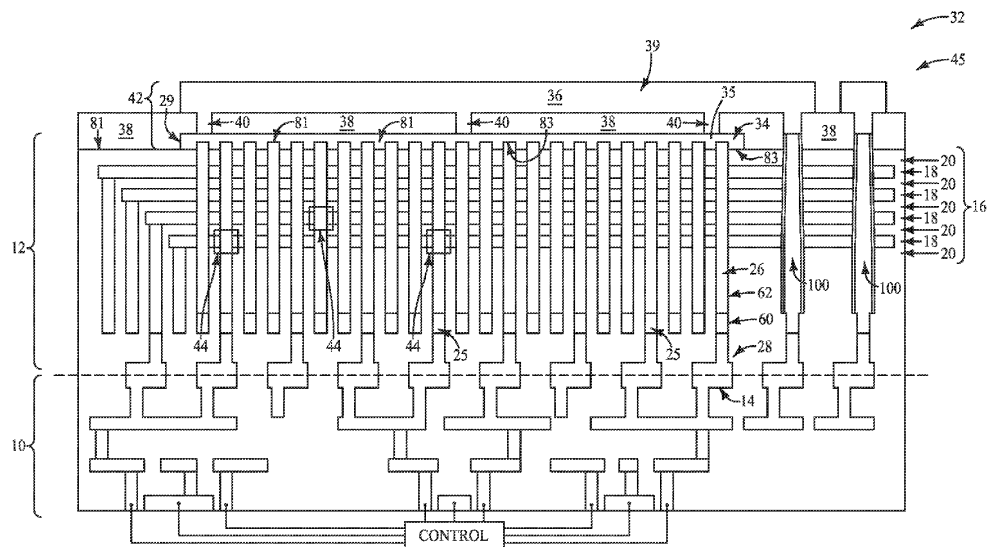


FIG. 8

(57) Abstract: Some embodiments include a method of forming a memory device. An assembly is formed to have channel structures extending through a stack of alternating insulative and conductive levels and into a first material under the stack. The assembly is inverted so that the first material is above the stack, and so that first regions of the channel structures are under the stack. At least some of the first regions are electrically coupled with control circuitry. At least some of the first material is removed, and second regions of the channel structures are exposed. Conductively-doped semiconductor material is formed adjacent the exposed second regions of the channel structures. Dopant is out-diffused from the conductively-doped semiconductor material into the channel structures. Some embodiments include memory devices (e.g., NAND memory assemblies).

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